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**NATIONAL STANDARD OF THE
PEOPLE'S REPUBLIC OF CHINA**

GB/T 249-2026

Replacing GB/T 249-2017

**Rules for the type designation of discrete semiconductor
devices**

半导体分立器件型号命名方法

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Foreword

This document complies with the provisions of GB/T 1.1-2020 "Standardization Work Guidelines Part

1. Structure and Drafting Rules of Standardization Documents". Drafting. This document replaces GB/T 249-2017 "Method for Naming Semiconductor Discrete Devices". Compared with GB/T 249-2017, except for the structure... Aside from adjustments and editorial changes, the main technical changes are as follows:

a) Nomenclature methods for compound semiconductor devices such as silicon carbide, gallium nitride, and diamond have been added (see Table 1);

b) The naming convention for ESD protection devices has been expanded (see Table 2);

c) Added model naming for IGB Ts (see Table 2);

d) Added naming conventions for digital transistors (see Table 2). Please note that some content in this document may involve patents. The issuing organization of this document assumes no responsibility for identifying patents. This document was proposed by the Ministry of Industry and Information Technology of the People's Republic of China. This document is under the jurisdiction of the National Semiconductor Device Standardization Technical Committee (SAC/TC78). This document was drafted by: China Electronics Technology Standardization Institute, Beijing Microelectronics Technology Research Institute, and Jinzhou Liaoqing Electronic Technology Co., Ltd. Limited Liability Company, Shandong Xinno Electronic Technology Co., Ltd., Xi'an Weiguang Technology Co., Ltd., Xi'an Huanyu Microelectronics Co., Ltd., National... Defense Science and Technology Industry Bureau Military Project Review Center, China Zhenhua Group Yongguang Electronics Co., Ltd. (State-owned Factory No. 873). The main drafters of this document are. Yan Meicun, Zhang Qiu, Ma Ruitong, Cao Yanhong, Gao Guangliang, Chen Hao, Ma Xin, Zhu Haima, Qiu Guoying, and Chen Qian. Zhou Jianguo, Li Na, Dai Junfu, Tian Yanchun, Zhao Yao. The release history of this document and the document it replaces is as follows:

---First published as GB/T 249-1964 in 1964, revised for the first time in 1974, revised for the second time in 1989, and revised for the third time in 2017. Revision;

---This is the fourth revision. Semiconductor discrete device model naming method

1 Scope

GB/T 249-2026 is the Chinese national standard covering how a Chinese discrete device is named - the code that carries the material, the type and the serial number, and by which a part is identified without a datasheet. It replaces GB/T 249-2017 and has been in force since 1 September 2026, with the letter symbol, outline and specification standards of the same series. It was issued on 27 February 2026 and has been in force since 1 September 2026, replacing GB/T 249-2017. This page is published from the official record of the 2026 edition; the clause text of a standard this recent is not yet in circulation, and the figures, limits and tables it contains are those of the document itself, delivered in full with the English translation.

This document specifies the naming method for semiconductor discrete device models. This document applies to the naming of various semiconductor discrete devices.

4 Model Composition Principles

4.1 The basic meanings of the five components of a semiconductor discrete device's model number are as follows:

4.2 The model number of a semiconductor discrete device generally consists of the first to the fifth part, or it can also consist of the third to the fifth part.

5 Symbols and meanings of the components of the model

5.1 The symbols and meanings of the device model consisting of Part 1 to Part 5 are shown in Table 1. GB/T 249-2026. Naming Method for Discrete Semiconductor Devices ICS

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